

S/N 08/903486

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: Donghee Kang

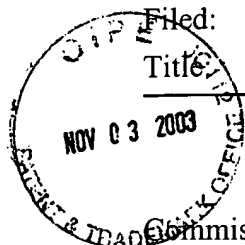
Serial No.: 08/903486

Group Art Unit: 2811

Filed: July 29, 1997

Docket: 303.326US1

Title: SILICON CARBIDE GATE TRANSISTOR



COMMUNICATION CONCERNING RELATED APPLICATION(S)

**RECEIVED**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

NOV 06 2003

Technology Center 2100

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
08/903452	July 29, 1997	303.324US1	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/256643	February 23, 1999	303.324US2	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/652420	August 31, 2000	303.324US3	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/691004	October 18, 2000	303.324US4	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/259870	March 1, 1999	303.326US2	FABRICATION OF SILICON CARBIDE GATE TRANSISTOR
08/902132 5886368	July 29, 1997	303.353US1	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
09/138294	August 21,	303.353US2	TRANSISTOR WITH SILICON

**RECEIVED**  
NOV 13 2003  
TECHNOLOGY CENTER 2800

COMMUNICATION CONCERNING CO-PENDING APPLICATIONS

Serial Number: 08/903486

Filing Date: July 29, 1997

Title: SILICON CARBIDE GATE TRANSISTOR

Page 2

Dkt: 303.326US1

6309907	1998		OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
08/902843	July 29, 1997	303.354US1	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
09/135413	August 14, 1998	303.354US2	METHOD FOR OPERATING A DEAPROM HAVING AN AMORPHOUS SILICON CARBIDE GATE INSULATOR
09/134713	August 14, 1998	303.354US3	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
08/902098 6031263	July 29, 1997	303.355US1	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/140978 6307775	August 27, 1998	303.355US2	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/141392 6249020	August 27, 1998	303.355US3	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/883795	June 18, 2001	303.355US4	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
10/047181	October 23, 2001	303.355US5	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
08/902133	July 29, 1997	303.356US1	DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE

COMMUNICATION CONCERNING CO-PENDING APPLICATIONS

Serial Number: 08/903486

Filing Date: July 29, 1997

Title: SILICON CARBIDE GATE TRANSISTOR

Page 3

Dkt: 303.326US1

10/231687	August 29, 2002	303.356US2	DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE
08/903453	July 29, 1997	303.378US1	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
09/258467	February 26, 1999	303.378US2	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
09/650553	August 30, 2000	303.378US3	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
10/461593	June 11, 2003	303.356US3	DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE

Respectfully submitted,

LEONARD FORBES ET AL.


By Applicants' Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

P.O. Box 2938

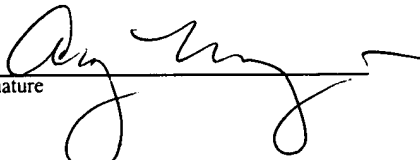
Minneapolis, MN 55402

(612) 373-6973

Date 31 October 2003 By   
Robert E. Mates  
Reg. No. 35,271

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner of Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 31st day of October, 2003.

Name Amy Moriarty

Signature 

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.  
Title: SILICON CARBIDE GATE TRANSISTOR

Docket No.: 303.326US1  
Filed: July 29, 1997  
Examiner: Donghee Kang  
Customer No.: 21186



Serial No.: 08/903486  
Due Date: October 31, 2003  
Group Art Unit: 2811  
Confirmation No.: 2304

2304#  
2123  
2811

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

RECEIVED

NOV 06 2003

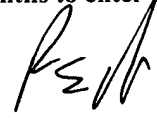
Technology Center 2100

We are transmitting herewith the following attached items (as indicated with an "X"):

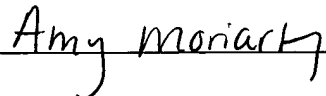
- ☒ A return postcard.
- ☒ An Amendment and Response (14 Pages).
- ☒ An Supplemental Information Disclosure Statement (2 pgs.), Form 1449 (3 pgs.), and copies of 54 cited documents.
- ☒ A check in the amount of \$180.00 to cover the fee for consideration of Information Disclosure Statement under 97(c).
- ☒ Communication Concerning Co-Pending Applications (3 pgs.).

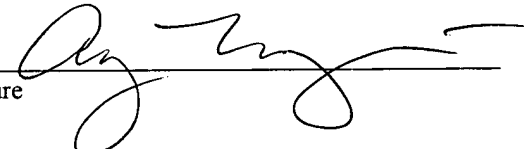
Please consider this a **PETITION FOR EXTENSION OF TIME** for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
Customer Number 21186

By:   
Atty: Robert E. Mates  
Reg. No. 35,271

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Non-Fee Amendment, Commissioner for Patents, P.O.Box 1450, Alexandria, VA 22313-1450, on this 31st day of October, 2003.

  
Name

  
Signature

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A. Customer Number 21186  
(GENERAL)

RECEIVED  
NOV 13 2003  
TECHNOLOGY CENTER 2800